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Sommario/riassunto	Nanostructured silicon-germanium (SiGe) opens up the prospects of novel and enhanced electronic device performance, especially for semiconductor devices. Silicon-germanium (SiGe) nanostructures reviews the materials science of nanostructures and their properties and applications in different electronic devices. The introductory part one covers the structural properties of SiGe nanostructures, with a further chapter discussing electronic band structures of SiGe alloys. Part two concentrates on the formation of SiGe nanostructures, with chapters on different methods of crystal growth such as mole